

PZTA42T1G

High Voltage Transistor Surface Mount

NPN Silicon

Features

- PZTA42T1G is Complement to PZTA92T1G
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage (Open Base)	V_{CEO}	300	Vdc
Collector-Base Voltage (Open Emitter)	V_{CBO}	300	Vdc
Emitter-Base Voltage (Open Collector)	V_{EBO}	6.0	Vdc
Collector Current (DC)	I_C	500	mAdc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 1)	P_D	1.5	W
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction Temperature	T_J	150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Device mounted on a FR-4 glass epoxy printed circuit board
1.575 in x 1.575 in x 0.0625 in; mounting pad for the collector lead = 0.93 sq in.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	83.3	$^\circ\text{C/W}$

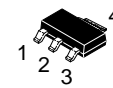
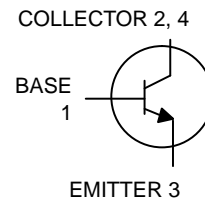
2. Device mounted on a FR-4 glass epoxy printed circuit board
1.575 in x 1.575 in x 0.0625 in; mounting pad for the collector lead = 0.93 sq in.



ON Semiconductor®

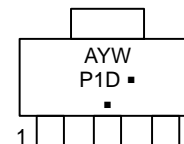
www.onsemi.com

SOT-223 PACKAGE NPN SILICON HIGH VOLTAGE TRANSISTOR SURFACE MOUNT



SOT-223
CASE 318E
STYLE 1

MARKING DIAGRAM



P1D = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
PZTA42T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
SPZTA42T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PZTA42T1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (Note 3) ($I_C = 1.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	300	–	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\text{ }\mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	300	–	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\text{ }\mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	6.0	–	Vdc
Collector-Base Cutoff Current ($V_{CB} = 200\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	0.1	μA
Emitter-Base Cutoff Current ($V_{BE} = 6.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	0.1	μA

ON CHARACTERISTICS

DC Current Gain ($I_C = 1.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 30\text{ mA}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	25 40 40	– – –	–
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DYNAMIC CHARACTERISTICS

Current-Gain – Bandwidth Product ($I_C = 10\text{ mA}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	50	–	MHz
Feedback Capacitance ($V_{CB} = 20\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{re}	–	3.0	pF
Collector-Emitter Saturation Voltage ($I_C = 20\text{ mA}$, $I_B = 2.0\text{ mA}$)	$V_{CE(sat)}$	–	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 20\text{ mA}$, $I_B = 2.0\text{ mA}$)	$V_{BE(sat)}$	–	0.9	Vdc

3. Pulse Test Conditions, $t_p = 300\text{ }\mu\text{s}$, $\delta = 0.02$.

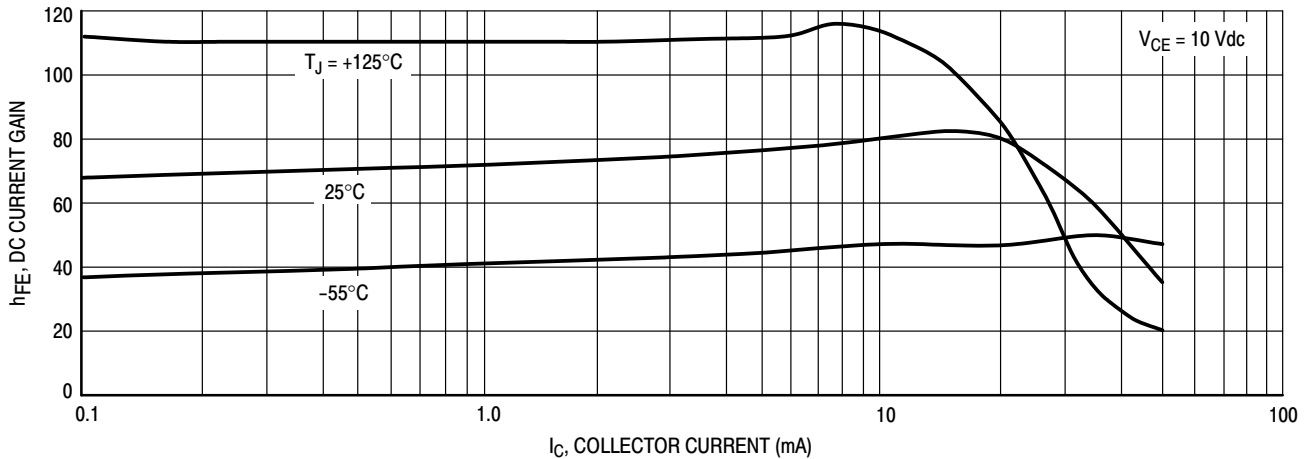


Figure 1. DC Current Gain

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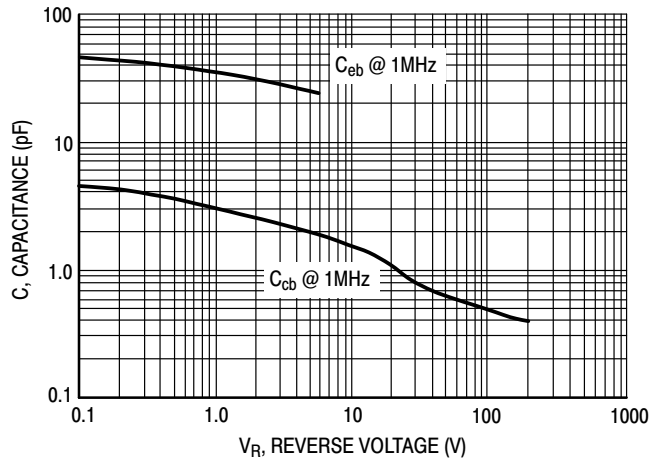


Figure 2. Capacitance

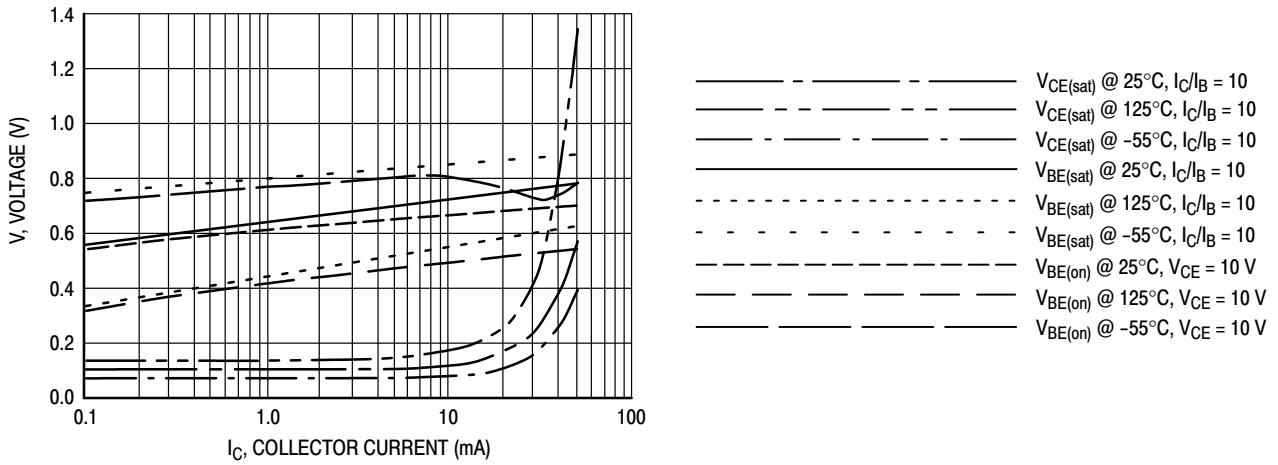


Figure 3. "ON" Voltages

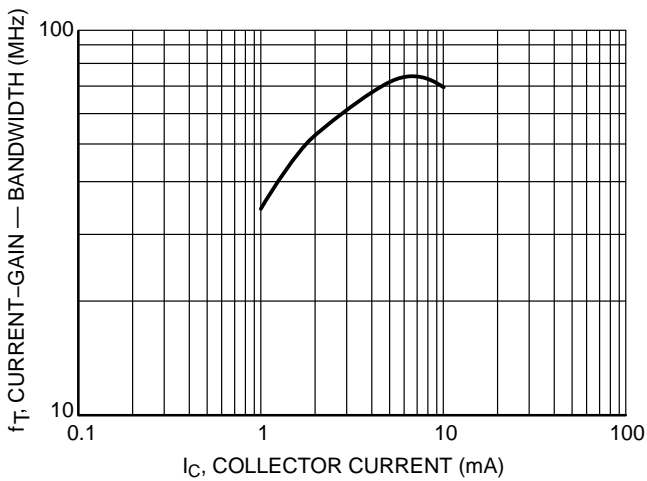


Figure 4. Current Gain Bandwidth Product

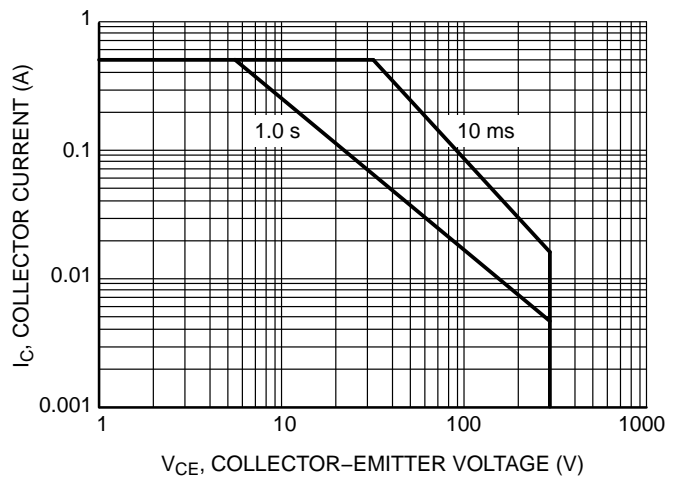
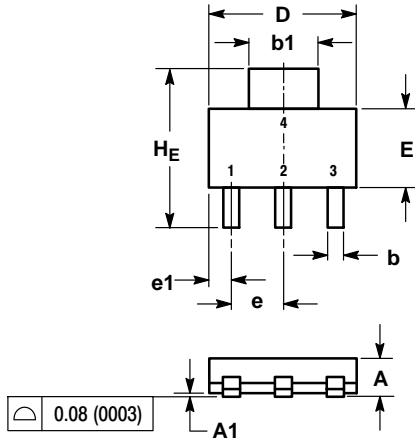


Figure 5. Safe Operating Area

PZTA42T1G

PACKAGE DIMENSIONS

SOT-223 (TO-261)
CASE 318E-04
ISSUE N

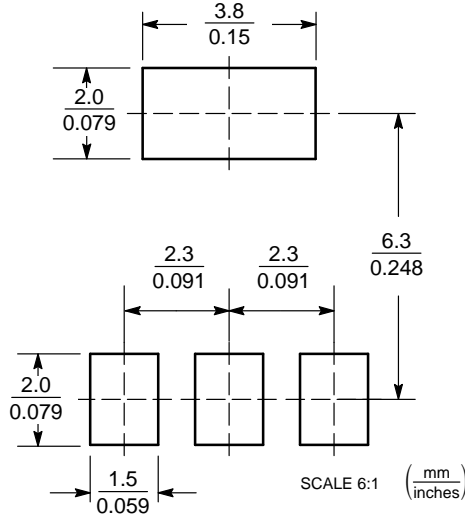


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	---	---	0.008	---	---
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	---	10°	0°	---	10°

- STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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